

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

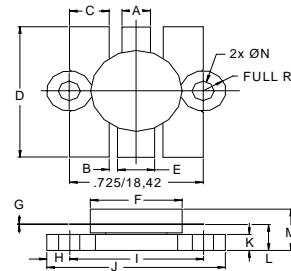
The **ASI J02015A** is Designed for High Power Class C Amplifier in, 225 to 400 MHz Military Communication Equipment.

**FEATURES:**

- Internal Input Matching Network
- $P_G = 8.4$  dB at 70 W/400 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	8.0 A
$V_{CBO}$	60 V
$V_{CEO}$	30 V
$V_{EBO}$	4.0 V
$P_{DISS}$	220 W @ $T_C = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	1.25 °C/W

**PACKAGE STYLE .500 6L FLG**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.150 / 3.43	.160 / 4.06
B	.045 / 1.14	
C	.210 / 5.33	.220 / 5.59
D	.835 / 21.21	.865 / 21.97
E	.200 / 5.08	.210 / 5.33
F	.490 / 12.45	.510 / 12.95
G	.003 / 0.08	.007 / 0.18
H	.125 / 3.18	
I	.725 / 18.42	
J	.970 / 24.64	.980 / 24.89
K	.090 / 2.29	.105 / 2.67
L	.150 / 3.81	.170 / 4.32
M	.285 / 7.24	
N	.120 / 3.05	.135 / 3.43

**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 50$ mA			30			V
$BV_{CES}$	$I_C = 50$ mA			60			V
$BV_{EBO}$	$I_E = 10$ mA			4.0			V
$I_{CBO}$	$V_{CB} = 30$ V					5.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V	$I_C = 2.0$ A		20		80	---
$C_{OB}$	$V_{CB} = 28$ V	$f = 1.0$ MHz				80	pF
$P_G$ $\eta_D$	$V_{CC} = 28$ V	$P_{OUT} = 70$ W	$f = 400$ MHz	8.4	60		dB %